



70V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D T _A = +25°C	
-70V	$160 \text{m}\Omega$ @ V_{GS} = - $10V$	-5.7A	
-700	$250 m\Omega$ @ V_{GS} = -4.5 V	-5.3A	

Description

This new generation of trench MOSFETs utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. The ZXMP7A17KQ is ideal for high efficiency, low voltage power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control
- Class D Audio Output Stages

Features and Benefits

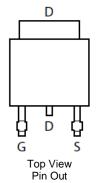
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- DPAK Package
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

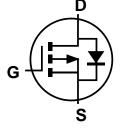
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208@3
- Weight: 0.315 grams (Approximate)



Top View





Equivalent Circuit

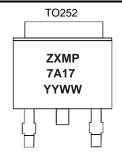
Ordering Information (Note 5)

Part Number	Case	Packaging
ZXMP7A17KQTC	TO252	2.500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP7A17 = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 10 = 2010) WW = Week (01 - 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	Drain-Source Voltage			-70	V
Gate-Source Voltage	Gate-Source Voltage			±20	V
		(Note 7)		-5.7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	I _D	-4.6	Α
		(Note 6)		-3.8	
Pulsed Drain Current	V _{GS} = 10V	(Note 8)	I _{DM}	-17.7	Α
Continuous Source Current (Body diode) (Note 7)		Is	-9.2	Α	
Pulsed Source Current (Body diode) (Note 8)		I _{SM}	-17.7	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	(Note 6)		4.17 33.3	
Power Dissipation Linear Derating Factor	(Note 7)	PD	9.25 74	W mW/°C
	(Note 9)		2.11 16.8	
	(Note 6)		30	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	13.5	°C/W
	(Note 8)		59.1	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ndition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-70	_	_	V	$I_D = -250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -70V, V _{GS} =	0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} =$	= 0V
ON CHARACTERISTICS						•	
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	_	_	V	I_{D} = -250 μ A, V_{DS} =	· V _{GS}
Static Drain Source On Registence (Note 10)				0.16	Ω	V _{GS} = -10V, I _D = -2	2.1A
Static Drain-Source On-Resistance (Note 10)	R _{DS(ON)}	_	_	0.25	12	V _{GS} = -4.5V, I _D = -	1.7A
Forward Transconductance (Notes 10 & 11)	9 _{fs}	_	4.4	_	S	V _{DS} = -15V, I _D = -2	2.1A
Diode Forward Voltage (Note 10)	V_{SD}	_	-0.85	-0.95	V	I _S = -2.0A, V _{GS} = 0	V, T _J = +25°C
Reverse Recovery Time (Note 11)	t _{rr}		29.8	_	ns	I _S = -2.1A, di/dt= 100A/µs	
Reverse Recovery Charge (Note 11)	Q _{rr}	_	38.5	_	nC		
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{iss}		635	_	pF	101/11	0) /
Output Capacitance	Coss		52	_	pF	V _{DS} = -40V, V _{GS} = f= 1MHz	UV
Reverse Transfer Capacitance	Crss		42.5	_	pF	TE TIMEZ	
Total Gate Charge (Note 12)	Q_g	_	9.6	_	nC	V _{GS} = -5V	
Total Gate Charge (Note 12)	Qg	_	18	_	nC		V _{DS} = -35V
Gate-Source Charge (Note 12)	Qgs	_	1.77	_	nC	V _{GS} = -10V	I _D = -2.1A
Gate-Drain Charge (Note 12)	Q_{qd}	_	3.66	_	nC	1	
Turn-On Delay Time (Note 12)	t _{D(on)}	_	2.5	_	ns		
Turn-On Rise Time (Note 12)	t _r		3.4	_	ns	V_{DD} = -35V, V_{GS} = -10V I_{D} = -1A, $R_G \cong 6.0\Omega$	
Turn-Off Delay Time (Note 12)	t _{D(off)}		27.9	_	ns		
Turn-Off Fall Time (Note 12)	t _f		8	_	ns		

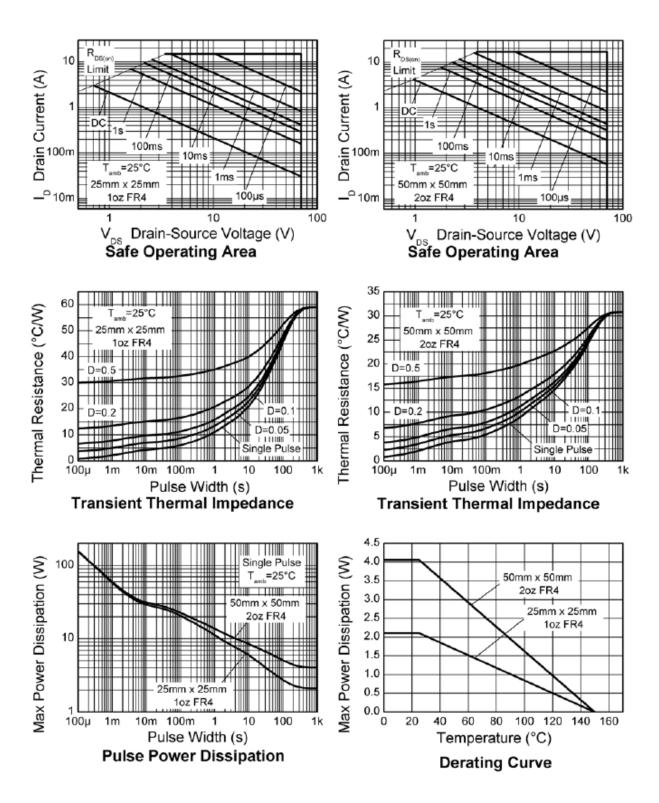
Notes:

- 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions. 7. For a device surface mounted on FR4 PCB measured at t ≤10 sec. 8. Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300µs pulse width limited by maximum junction temperature. 9. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

- 10. Measured under pulsed conditions. Pulse width ≤300µs; duty cycle ≤ 2%.
- 11. Switching characteristics are independent of operating junction temperature.
- 12. For design aid only, not subject to production testing.

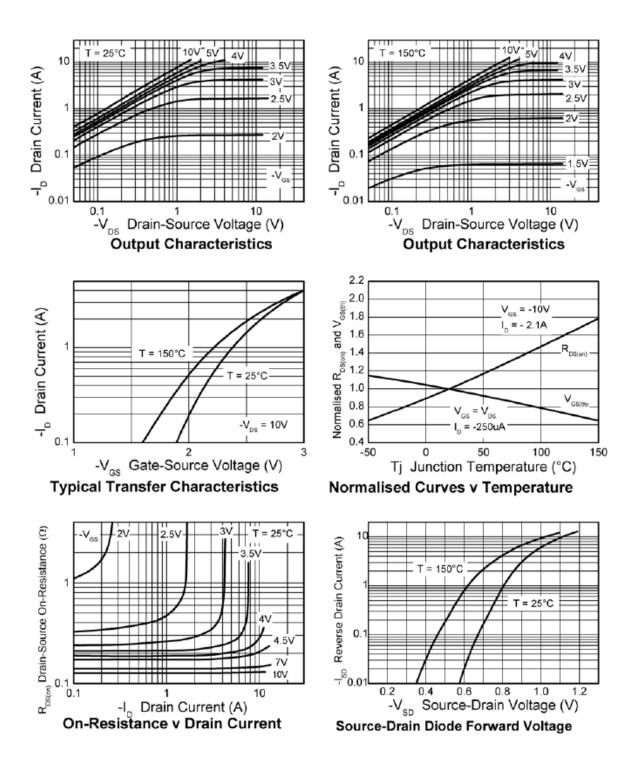


Thermal Characteristics



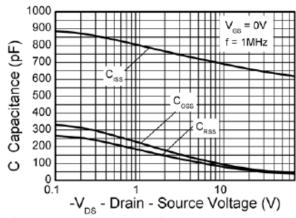


Typical Characteristics

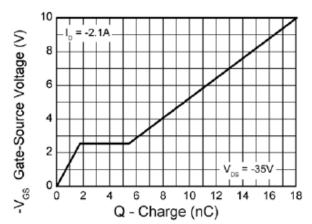




Typical Characteristics (cont.)



Capacitance v Drain-Source Voltage

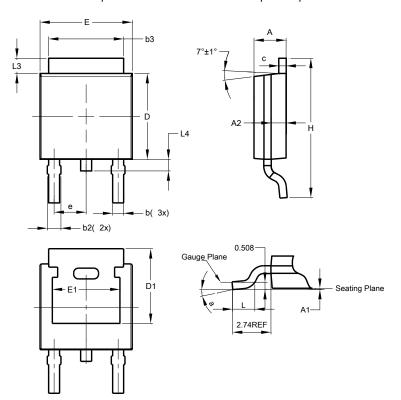


Gate-Source Voltage v Gate Charge



Package Outline Dimensions

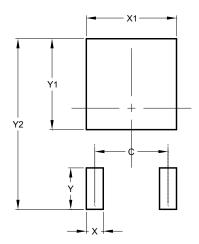
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	4.572		
X	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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